Dual N-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	30V
● I_D	32A
● $R_{DS(ON)}$(at V	

■ Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Units

■Typical Electrical and Thermal Characteristicv2yiagrams

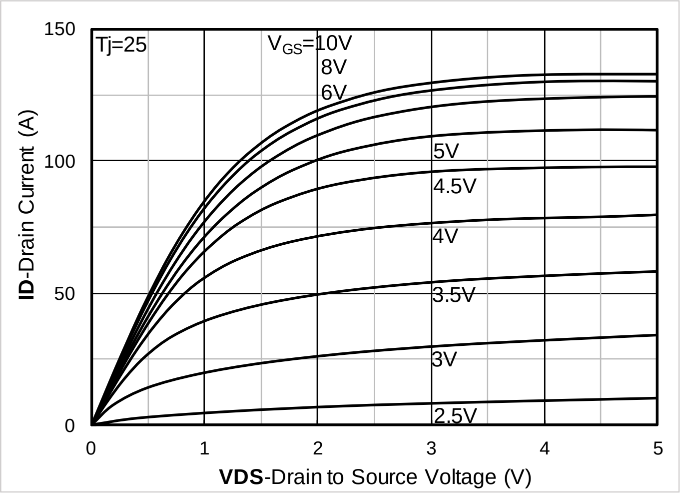


Figure 1. Output Characterivtics; typical values

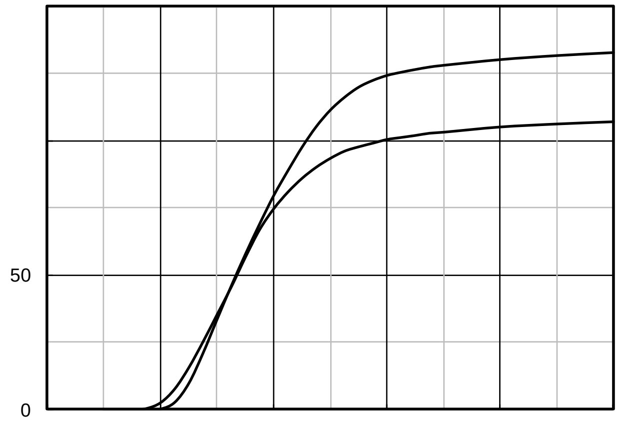


Figure 2. Tranvfer Characterivtics; typical values

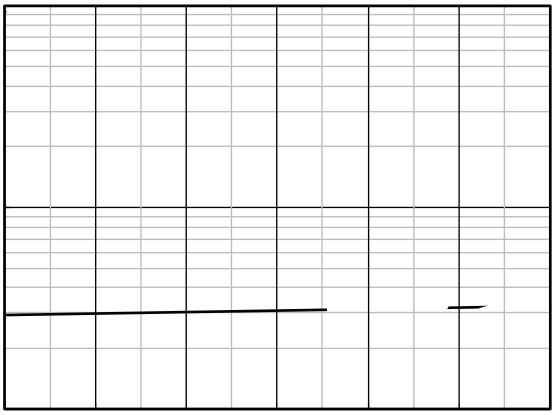


Figure 3. Capacitance Characterivtics; typical valuev

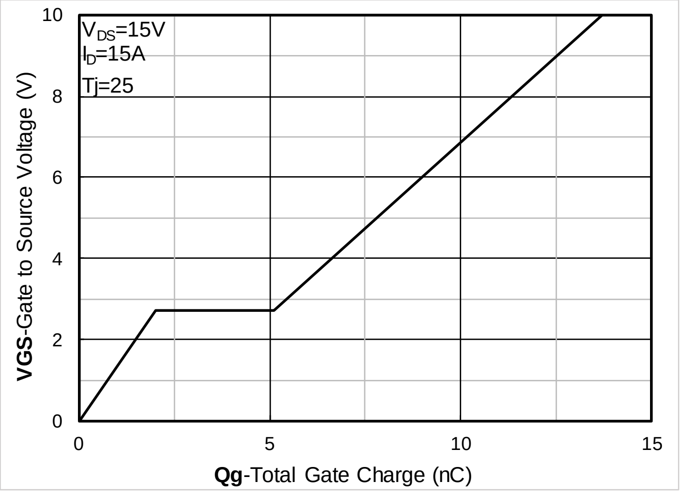


Figure 4. Gate Charge; typical values

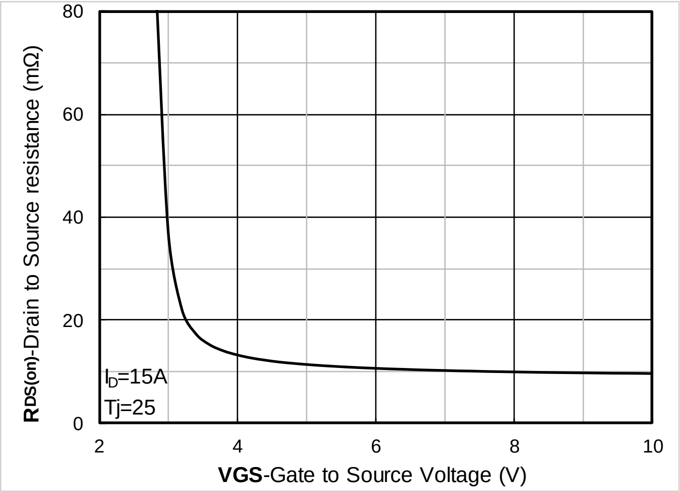


Figure 5. On-Resivtance vs. Gate to Source Voltage; typical valuev

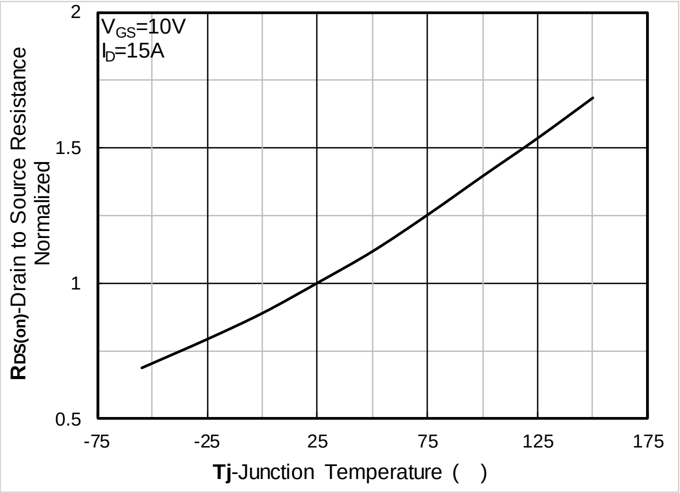
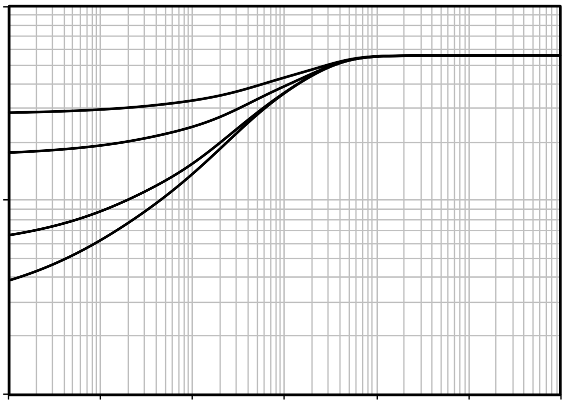


Figure 6. Normalized On-Resivtance



■ Test Circuits & Waveforms

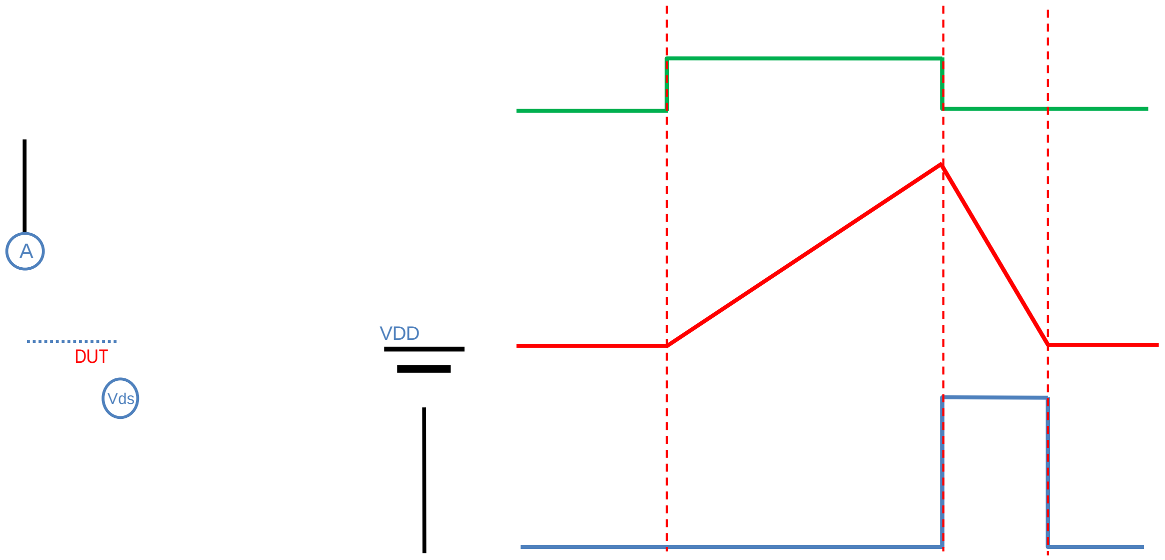


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

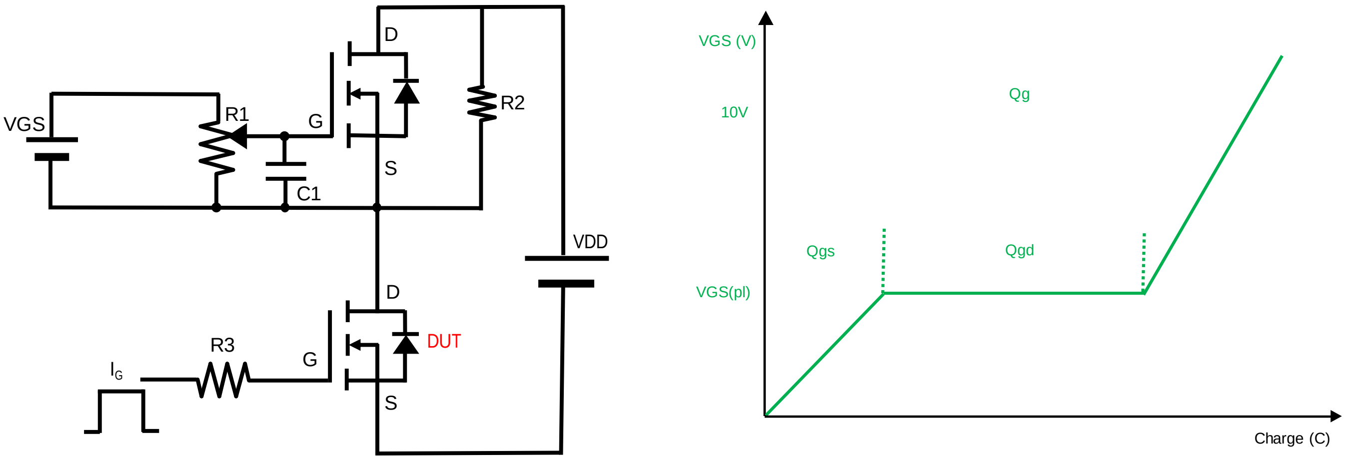


Figure B. Gate Charge Test Circuit & Waveform

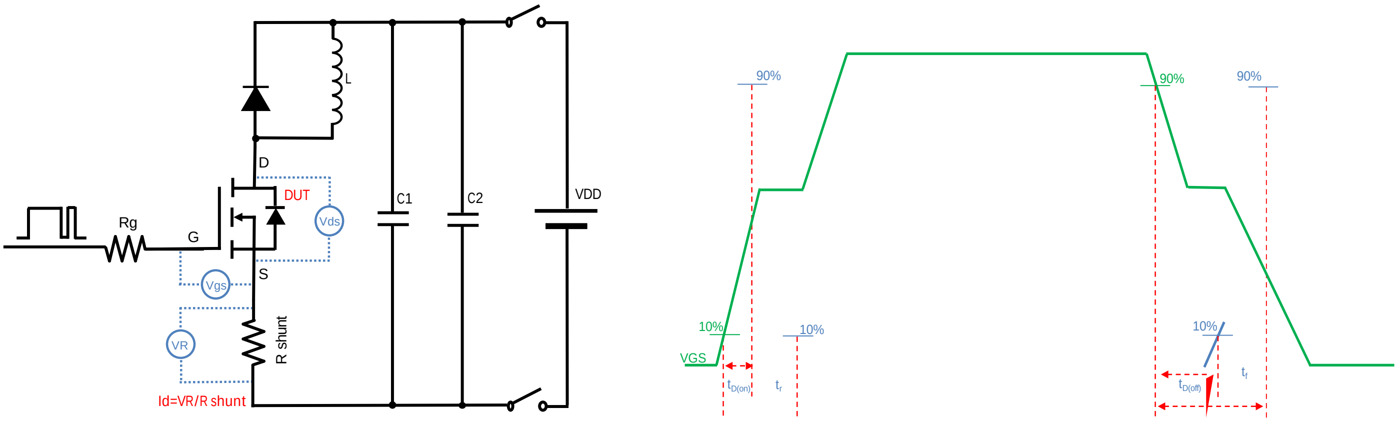


Figure C. Resistive Switching Test Circuit & Waveform

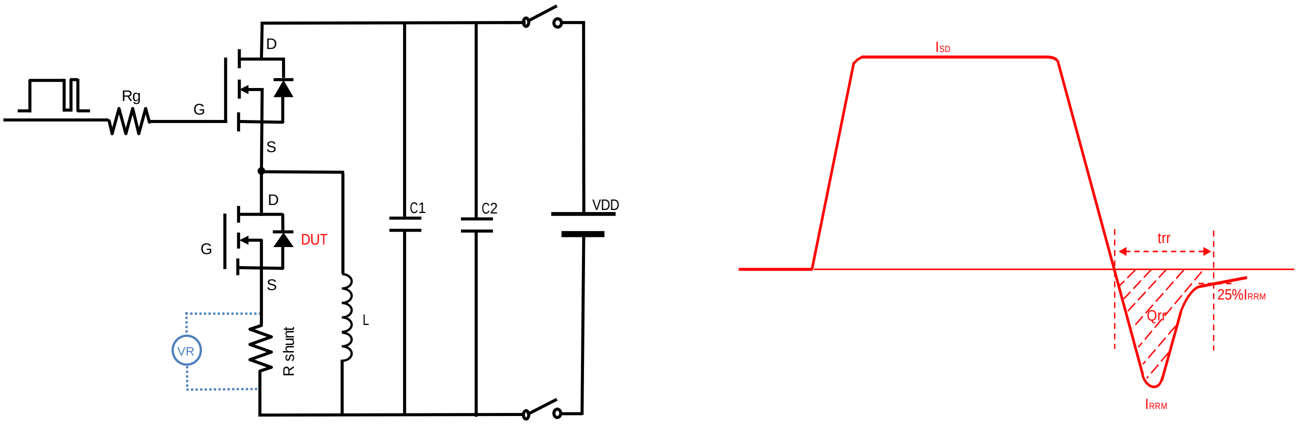
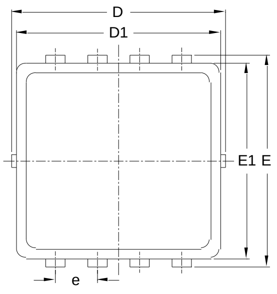
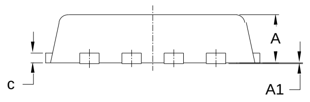


Figure D. Diode Recovery Test Circuit & Waveform

■ PDFN3333-8L-Dual Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.028	0.033	0.700	0.850
A1	0.000	0.002	0.000	0.050
b	0.008	0.016	0.200	0.400
c	0.004	0.010	0.100	0.250
D	0.124	0.136	3.150	3.450
D1	0.118	0.130	3.000	3.300
D2	0.033	0.049	0.840	1.240
D3	0.089	0.104	2.250	2.650
E	0.124	0.136	3.150	3.450
E1	0.114	0.126	2.93.029 Tm -0.00929 Tc[E1)]TJET2	



UNIT mm

NOTE:
1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

1.840

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